60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI3333-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
60V	50mΩ @ V_{GS} = 10V	18A
	63mΩ @ V_{GS} = 4.5V	15A

Features and Benefits

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low $R_{DS(ON)}$—Ensures Minimal On-State Losses
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Wettable Flank for Improved Optical Inspections
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-products/.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**

Description and Applications

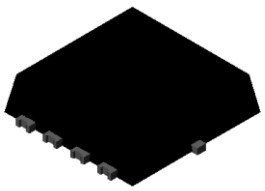
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power-Management Functions
- DC-DC Converters

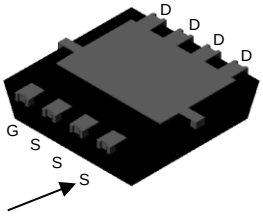
Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (Approximate)

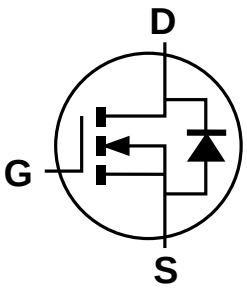
PowerDI3333-8 (SWP) (Type UX)



Top View



Pin1 Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH6069SFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMNH6069SFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

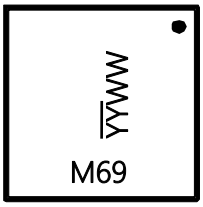
Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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Marking Information



M69 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current V_{GS} = 10V (Note 5)	Steady State	T_A = +25°C T_A = +100°C	I_D	5.0 3.5	A
Continuous Drain Current V_{GS} = 10V (Note 6)	Steady State	T_C = +25°C T_C = +100°C	I_D	18 12	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I_{DM}	72	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	5.0	A
Pulsed Source Current (380µs Pulse, Duty Cycle = 1%)			I_{SM}	72	A
Avalanche Current , L = 0.1mH			I_{AS}	12	A
Repetitive Avalanche Energy , L = 0.1mH			E_{AS}	7.2	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	3.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	50	°C/W
Total Power Dissipation (Note 6)		P_D	38	W
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	3.9	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	35	50	mΩ	V_{GS} = 10V, I_D = 3A
		—	41	63		V_{GS} = 4.5V, I_D = 2.4A
Diode Forward Voltage	V_{SD}	—	0.8	1.1	V	V_{GS} = 0V, I_S = 2.5A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	740	—	pF	V_{DS} = 30V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	40	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	28	—	pF	
Gate Resistance	R_g	—	2.2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	6.4	—	nC	V_{DS} = 30V, I_D = 12A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	14	—	nC	
Gate-Source Charge	Q_{gs}	—	2.8	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.3	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.6	—	ns	V_{DS} = 30V, I_D = 12A, V_{GS} = 10V, R_G = 6.0Ω
Turn-On Rise Time	t_R	—	5.0	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	12	—	ns	
Turn-Off Fall Time	t_F	—	3.3	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	11	—	ns	I_F = 4.5A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q_{RR}	—	5.1	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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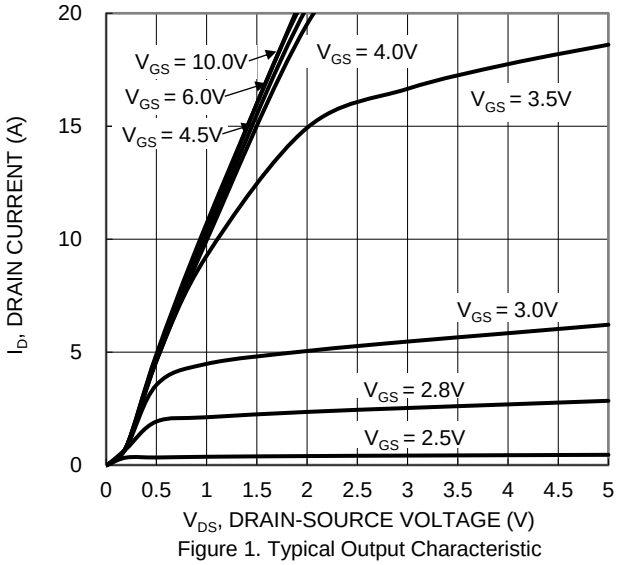


Figure 1. Typical Output Characteristic

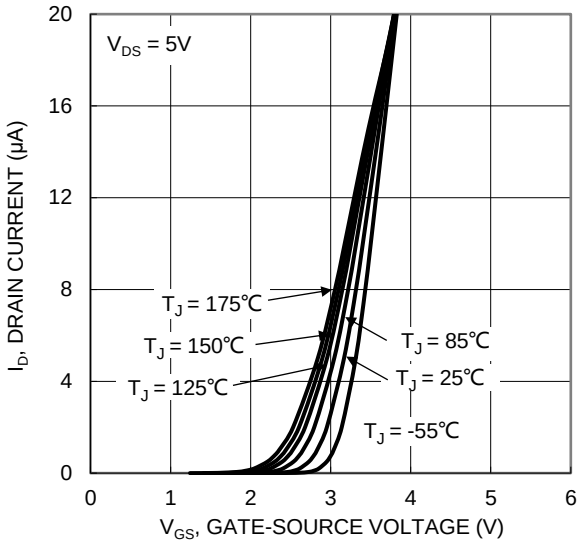


Figure 2. Typical Transfer Characteristic

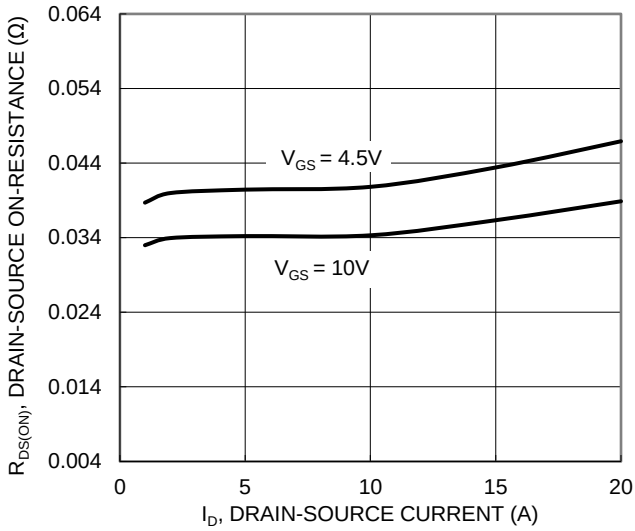


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

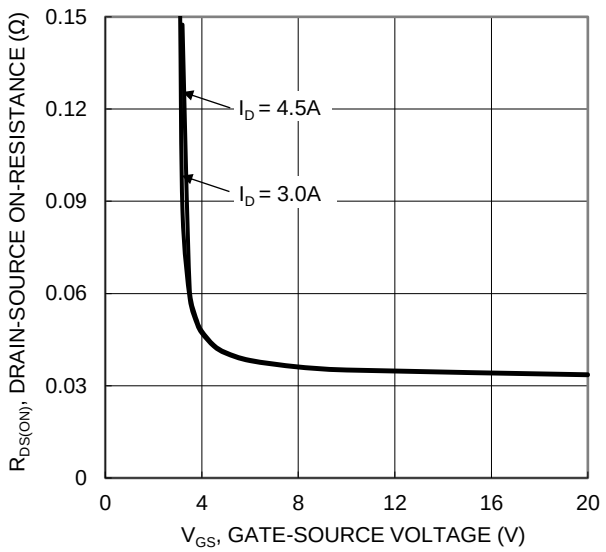


Figure 4. Typical Transfer Characteristic

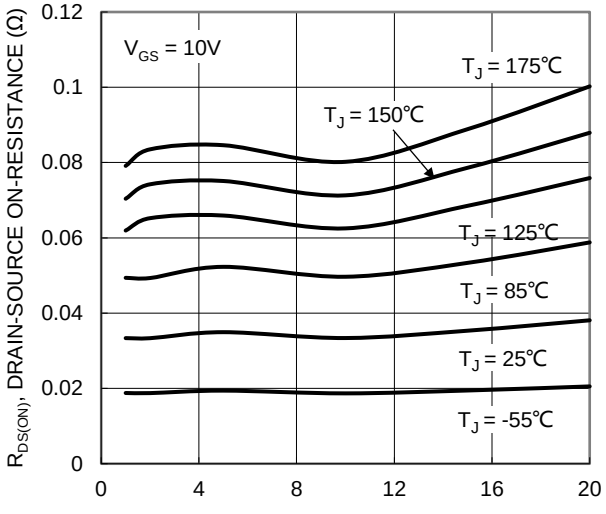


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

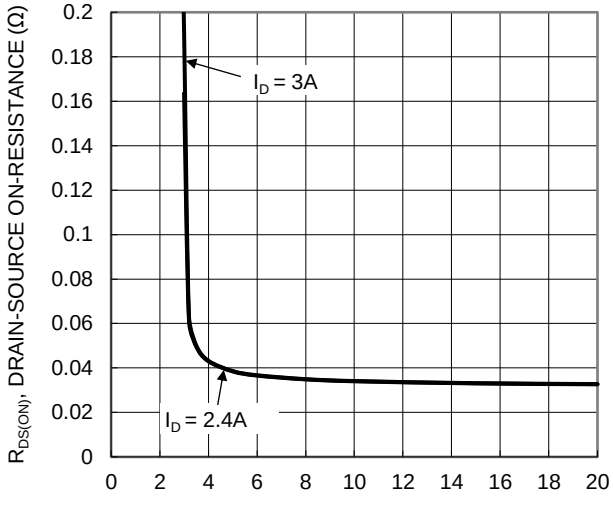


Figure 4. Typical Transfer Characteristic

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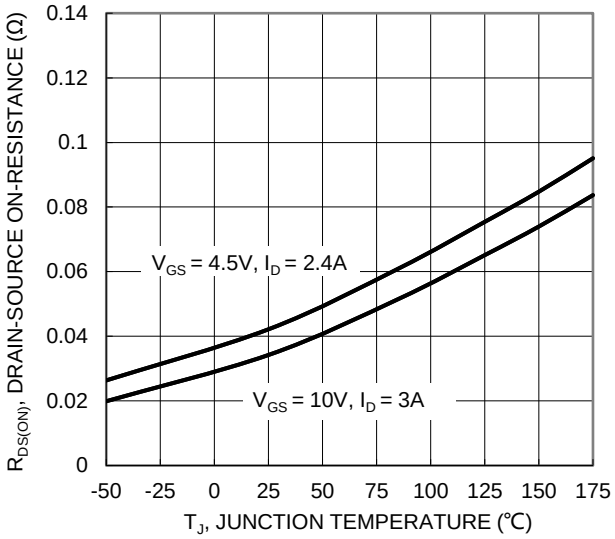


Figure 7. On-Resistance Variation with Temperature

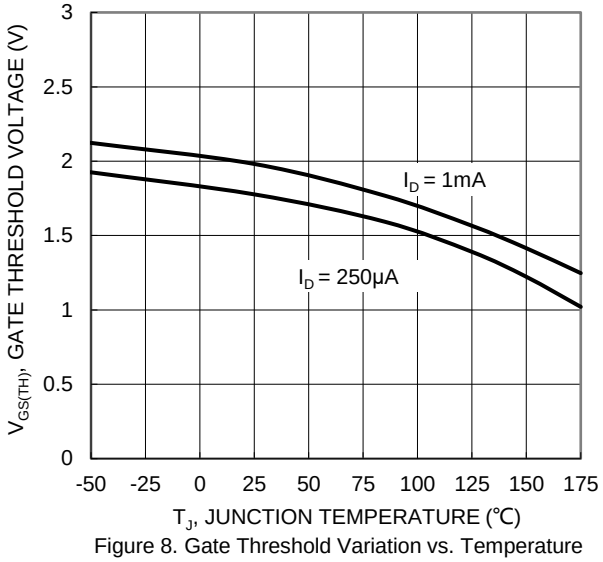


Figure 8. Gate Threshold Variation vs. Temperature

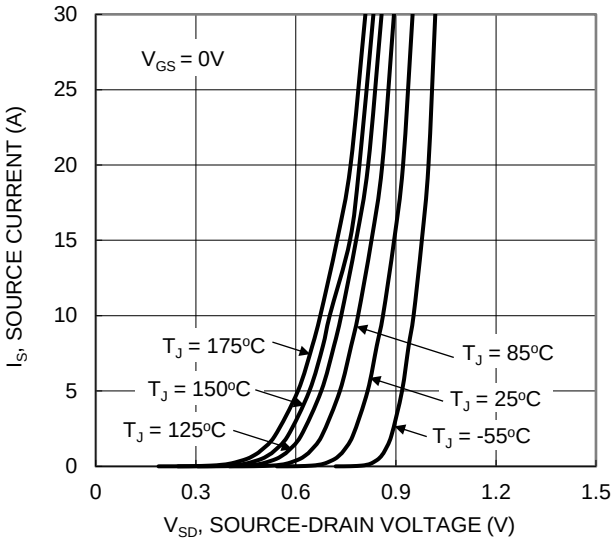


Figure 9. Diode Forward Voltage vs. Current

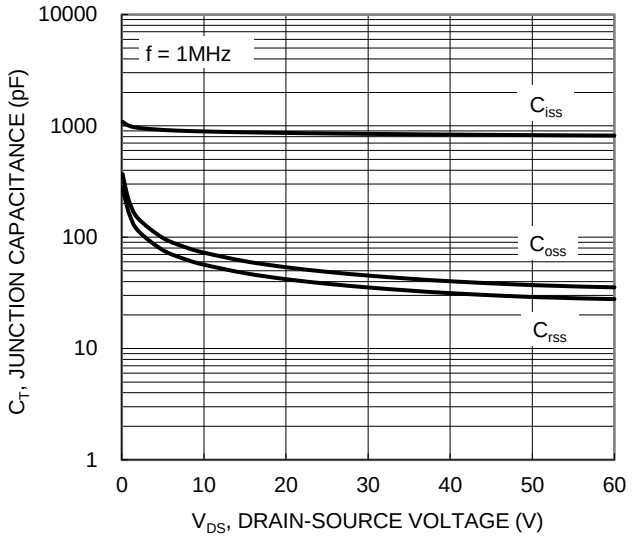


Figure 10. Typical Junction Capacitance

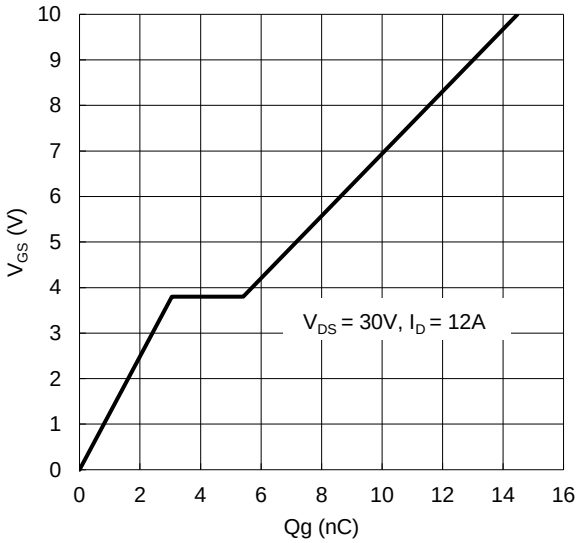


Figure 11. Gate Charge

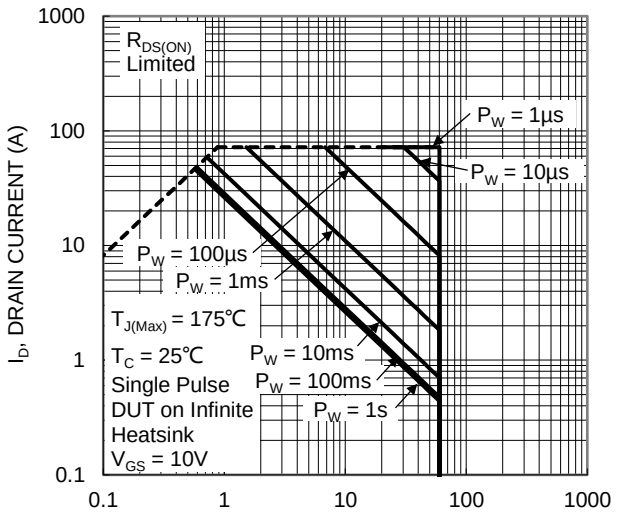


Figure 12. SOA, Safe Operation Area

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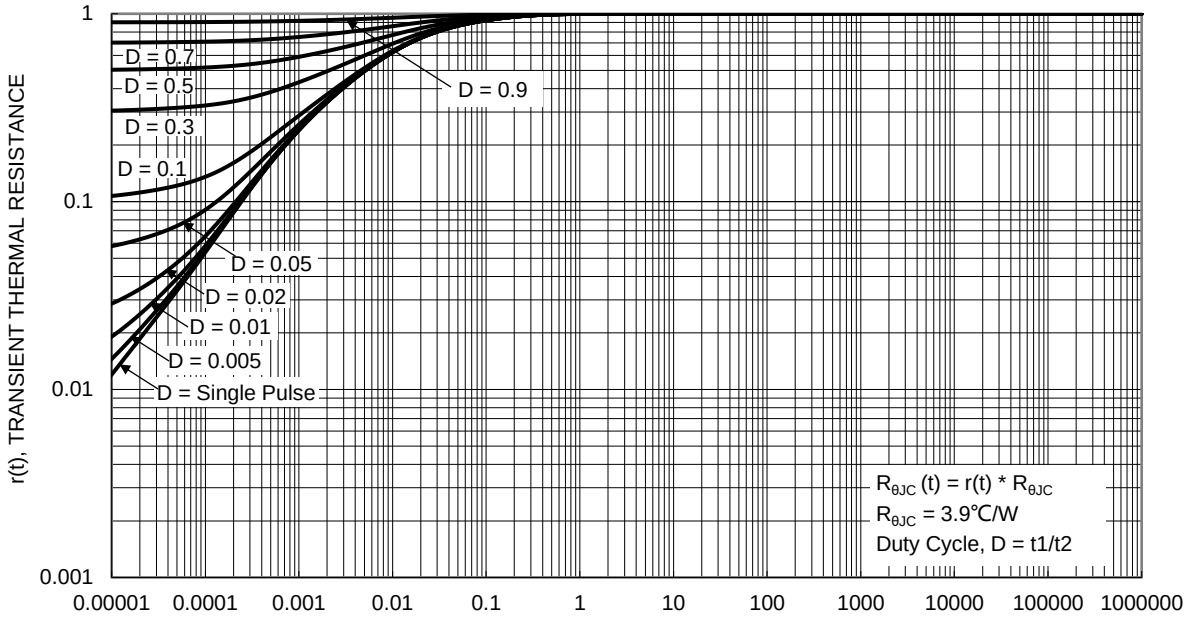


Figure 13. Transient Thermal Resistance

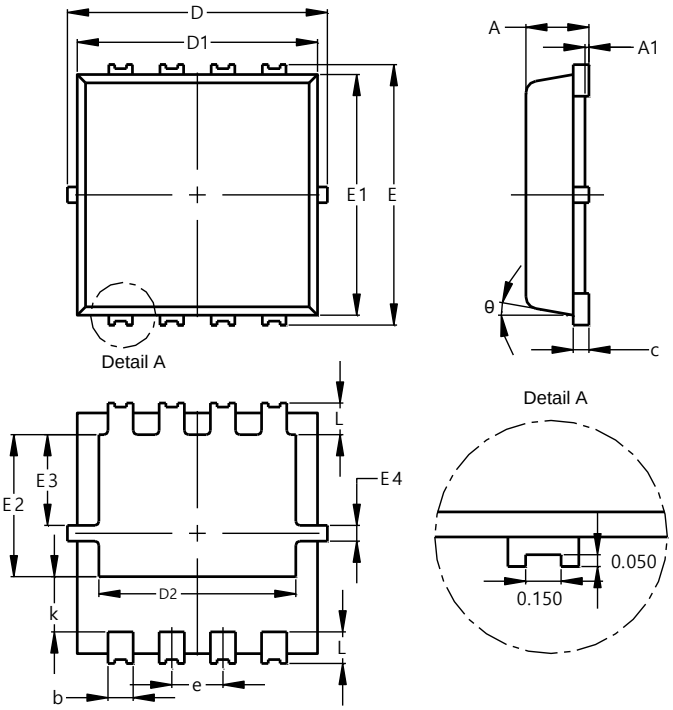
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

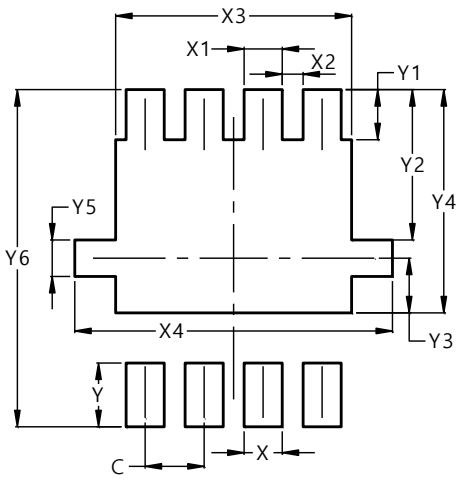


PowerDI3333-8 (SWP) (Type UX)			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	—
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	—	—	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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